

REMARKS

Claims 1-24 and 26-39 are pending in application. Claims 1- 4, 14 – 24, 27, 30-38 have been amended, and claim 25 has been cancelled. No new matter has been introduced by the amendment. Support for the subject matter of amended claims 1 and 24 can be found in original claims 1 and 24, in original claim 25, and in the applicants' specification, for example, at page 7, lines 8 to 23.

Claim Objection

Claims 1-23 were subject to objection for use for the improper plural form of the term "transistor." This objection is overcome in view of the amendment of claims 1 and 23 to replace the term "transistors" with the term "transistor."

Rejection Under 35 U.S.C. §112, second paragraph

Claims 1-39 have been rejected for including terms that indicate possibility or probability. This rejection is overcome in view of the amendment of independent claims 1, 23 and 24, and dependent claims 2-3. In these claims, the terms "can be" have been replaced by present tense expressions.

Claim 5 has been amended to improve its form.

Claim 23 was indicated as allowable if rewritten to overcome the rejection under Section 112. The applicants assert that claim 23 is in condition for allowance in view of the amendment.

Rejection Under 35 U.S.C. §102(b)

Claim 1, 2, 5-12, 14, 18, 24-25, 28, 30, 34, and 39 have been rejected over *Gerzberg* (US 4,590,589). This rejection is overcome in view of the amendment of claims 1 and 24 together with the following remarks.

Claim 1, as amended, recites, an integrated read-only memory that comprises, *inter alia*:

“a common layer between the drain connections and the electrode electrically linking the drain connections to the electrode, wherein the electrical resistance of the layer is changeable by a configuration voltage or a configuration current;”

Claims 2-4 and 14-22 have been amended to correspond with the amendment of claim 1 from which they directly or indirectly depend.

Claim 24 has been amended in a manner analogous to the amendment of claim 1. Claim 24, as amended, recites a method for producing an integrated read-only memory that comprises, *inter alia*:

“providing a common layer between the drain connections and the electrode electrically linking the drain connections to the electrode, wherein the electrical resistance of the common layer is changeable by a configuration voltage or a configuration current;”

The applicants assert that claims 1 and 24 distinguish over *Gerzberg* at least because *Gerzberg* does not suggest or disclose a common layer between the drain connections and the electrode, wherein the electrical resistance of the layer is changeable by a configuration voltage or a configuration current. The claimed common layer is patentably distinguishable from programmable resistor of *Gerzberg*.

Claims 27 and 30-38 have been amended to correspond with the amendment of claim 24, from which they directly or indirectly depend.

The applicants assert that claims 2-22 are allowable in view of the amendment and remarks pertaining to claim 1, from which they directly or indirect depend. And, claims 26-39 are allowable in view of the amendment and remarks pertaining to claim 24, from which they directly or indirect depend.

The Applicants have made a novel and non-obvious contribution to the art of integrated read-only memory devices and their operation. The claims at issue are

distinguishable over the cited references and are in condition for allowance. Accordingly, such allowance is now earnestly requested.

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